Abstract

Provided are a sputtering target and a method for manufacturing the same for suppressing sputtering-related problems. A sputtering target comprising a binary alloy of Cu and Al, with the balance consisting of unavoidable impurities, wherein:

Cu and Al contents (at%) satisfy the following condition:

$0.48 \leq Al/(Cu+Al) \leq 0.70$, and

the sputtering target satisfies at least one of the following conditions (1) through (3):

(1) $0.48 \leq Al/(Cu+Al) < 0.55$, and the pore area fraction within the field of view when observed by SEM is 2.0% or less;

(2) $0.55 \leq Al/(Cu+Al) \leq 0.70$, and the pore area fraction within the field of view when observed by SEM is 1.0% or less;

(3) an oxygen content of the sputtering target is 1,000 ppm by mass or less, and flexural strength is 70 MPa or greater.

(Figure 4)